

THVD8000T RS-485 Transceiver with OOK Modulation and Extended Temperature Range for Power Line Communication

1 Features

- 3V to 5.5V supply voltage
- Half-duplex communication
 - Up to 500kbps data rate with f_0 / bps = 10
 - Higher data rates are possible with f₀ / bps < 10
- RS-485 electrical signaling with on-off keying (OOK) modulation
- Pin selectable carrier frequency: 125kHz to 5MHz
- Spread spectrum clocking for excellent EMI performance
- Polarity free
- TX timeout to avoid stuck bus conditions
- Operational common-mode range: -7V to 12V
- Bus I/O protection
 - ± 18V DC fault protection
 - ± 16kV HBM ESD
 - ± 8kV IEC 61000-4-2 contact discharge
 - ± 15kV IEC 61000-4-2 air gap discharge
 - ± 4kV IEC 61000-4-4 fast transient burst
- Extended temperature range: -55°C to 125°C
- 8-Pin SOT-23 package for space constrained applications

2 Applications

- **HVAC** systems
- **Building automation**
- Factory automation & control
- **Appliances**
- Lighting
- Grid infrastructure
- Power delivery

3 Description

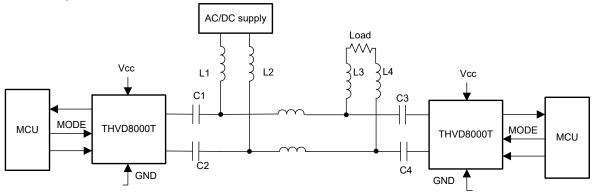
THVD8000T is an RS-485 transceiver with on-off keying (OOK) modulation and demodulation built in for power line communication. Modulating data onto existing power lines allows power delivery and data communication to share a common pair of wires, resulting in a reduction of the system cost.

A pin programmable interface simplifies the system design. The carrier frequency can be adjusted by changing an external resistor on the F SET pin. A broad range of carrier frequencies gives the system designer the flexibility to choose the external inductors and capacitors. OOK modulation also operates with immunity to data polarity for ease of system installations.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾		
THVD8000T	SOT-23-THN (8)	2.9mm × 2.8mm		

- For more information, see Section 11.
- The package size (length × width) is a nominal value and includes pins, where applicable.



Simplified Schematic



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4 Pin Configuration and Functions

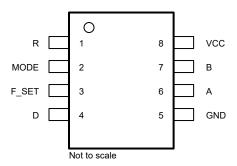


Figure 4-1. DDF Package, 8-Pin SOT-23 (Top View)

Table 4-1. Pin Functions

PIN NAME NO.		TYPE	DESCRIPTION	
		ITPE	DESCRIPTION	
R	1	Digital output	In receiver mode, R pin operates as an output, in transmit mode, it enters a high impedance state. Pull-up resistor is recommended if the MODE pin is toggled.	
MODE 2 Digital input Transmit and receive mode selection. Low = receive mode; High = transmit 2MΩ pull-down to GND		Transmit and receive mode selection. Low = receive mode; High = transmit mode. $2M\Omega$ pull-down to GND		
F_SET	3	Analog input	Carrier frequency selection. Use a resistor to GND to select a frequency.	
D	4	Digital input	Driver data input, $2M\Omega$ pull-up to V_{CC}	
GND	5	Ground	Device ground	
Α	6	Bus input/output	Bus I/O port A (complementary to B)	
В	7	Bus input/output	Bus I/O port B (complementary to A)	
V _{CC}	8	Power	3.3V to 5V device supply	



5 Specifications

5.1 Absolute Maximum Ratings

see (1)

		MIN	MAX	UNIT
V _{CC}	Supply voltage	-0.5	7	V
V _L	Input voltage at any logic pin (D, MODE or F_SET)	-0.3	5.7	V
V _A , V _B	Voltage at A or B inputs (differential or with respect to GND)	-18	18	V
Io	Receiver output current	-24	24	mA
TJ	Junction temperature		170	°C
T _{STG}	Storage temperature	-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

5.2 ESD Ratings

				VALUE	UNIT
	Electrostatic discharge	Homes had and delivered (UDM) are ANGUEGRA (UEREG IG 004(1)	A and B pins to GND	±16,000	
V _(ESD)		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	All pins	±4,000	V
- (ESD)		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	All pins	±1,500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 ESD Ratings - IEC Specifications

			VALUE	UNIT
		IEC 61000-4-2 ESD contact discharge, A and B pins to GND	±8	
V _(ESD)	Electrostatic discharge	IEC 61000-4-2 ESD air gap discharge, A and B pins to GND	±15	kV
		IEC 61000-4-4 electrical fast transient, A and B pins to GND	±4	

5.4 Recommended Operating Conditions

			MIN	NOM MAX	UNIT
V _{CC}	Supply voltage		3	5.5	V
V _{ID}	Input differential voltage (A and B pins)		-7	12	V
V _{CM}	Operational common mode voltage (A an	d B pins)	-7	12	V
V _{IH}	High-level input voltage (D and MODE pir	ns)	2	V _{CC}	V
V _{IL}	Low-level input voltage (D and MODE pin	s)	0	0.8	V
	Output current	Driver	-60	60	A
I _O		Receiver	-4	4	mA
R _{F_SET}	Carrier frequency selection resistor		1.5	80	kΩ
ΔR_{F_SET}	Carrier frequency selection resistor tolera	nce	-2	2	%
1/t _{UI}	Data rate	Modulation mode ⁽¹⁾		f ₀ / 10	bps
C _{F_SET}	Recommended load capacitance on F_SI	ET pin		100	pF
T _A	Operating ambient temperature		- 55	125	°C

(1) f₀ is the carrier frequency (in Hz) set by the external resistor between F_SET and GND pins.

5.5 Thermal Information

		THVD8000T	
	THERMAL METRIC ⁽¹⁾		UNIT
		8 PINS	
R _{0JA}	Junction-to-ambient thermal resistance	106.6	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	38.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	29.9	°C/W
ΨЈТ	Junction-to-top characterization parameter	29.5	°C/W
ΨЈВ	Junction-to-top characterization parameter	29.5	°C/W

⁽¹⁾ For more information about traditional and new thermalmetrics, see the Semiconductor and ICPackage Thermal Metrics application report.

5.6 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted). All typical values are at 25° C and supply voltage of $V_{CC} = 5 \text{ V}$.

	PARAMETER	TEST CONDITION	NS	MIN	TYP	MAX	UNIT
Driver							
		OOK mode, R _L = 60Ω , $-7 V \le V_{test} \le 12 V$, Measured at 2nd pulse	See Figure 6-1	1.5	3.5		
Vopl Voc Voc(PP) OS OCDf0 Mfssc	Driver differential output voltage magnitude	OOK mode, R_L = 100 Ω , C_L = 50 pF, Measured at 2nd pulse	See Figure 6-1	2	4		V
		OOK mode, R_L = 54 Ω , C_L = 50 pF, Measured at 2nd pulse	See Figure 6-1	1.5	3.5		
V _{OC}	Steady state common-mode output voltage	OOK mode, R_L = 60 Ω , C_L = 50 pF	See Figure 6-2	1	V _{CC} / 2	3	V
ΔV _{OC}	Change in differential driver common-mode output voltage	OOK mode, $R_L = 60 \Omega$, $C_L = 50 pF$	See Figure 6-2	-160		160	mV
V _{OC(PP)}	Peak-to-peak driver common- mode output voltage	OOK mode, R_L = 60 Ω , C_L = 50 pF, V_{CC} = 3.3 V and V_{CC} = 5V	See Figure 6-2		425		mV
Ios	Driver short-circuit output current	OOK mode, MODE = V _{CC} , −7 V ≤ [V_A or V_B] $\leq 12 \text{ V}$	-250		250	mA
,	Minimum carrier frequency ⁽¹⁾	R_{F_SET} = 77 k Ω	G E: 0.0		125		kHz
f ₀	Maximum carrier frequency ⁽¹⁾	R_{F_SET} = 1.5 k Ω	See Figure 6-3		5		MHz
DCD _{f0}	Carrier frequency duty cycle distortion	Measured over the full range of f ₀		-2		2	%
Δf_0	Carrier frequency tolerance	Measured with a ±2% tolerant R _{F_S}	Measured with a ±2% tolerant R _{F SET}			25	%
Δf_{SSC}	Variation of the carrier frequency for spread spectrum clocking	Measured across the full carrier free	fleasured across the full carrier frequency range		±5		%
f _{SSC}	Spread spectrum clock rate				30		kHz



over operating free-air temperature range (unless otherwise noted). All typical values are at 25° C and supply voltage of $V_{CC} = 5 \text{ V}$.

	PARAMETER	TEST CONDITION	NS	MIN	TYP	MAX	UNIT
Receiver							
	Bus input current in receive	MODE - OND V - OV F F V	V _I = 12 V		75	125	
l _l	mode	MODE = GND, $V_{CC} = 0 \text{ V or } 5.5 \text{ V}$	V _I = -7 V	-97	-70		μA
	OOK signal differential swing	12	125 kHz			225	
V _{MAG_ZERO}	(magnitude) to detect a zero at		1 MHz			150	mV
	the R output		5 MHz			115	
	OOK signal differential swing		125 kHz	20			
V_{MAG_ONE}	(magnitude) to detect a one at	MODE = GND, over full common mode range	1 MHz	10			mV
	the R output	- mous range	5 MHz	10			
			125 kHz	40			
V_{MAG_HYS}	Receiver differential input voltage threshold hysteresis		1 MHz	20			mV
			5 MHz	20			
Logic / Contr	ol Pins						
I _{IN}	Input current (D, MODE)	V _O = 0 V or V _{CC}	$V_O = 0 \text{ V or } V_{CC}$			5	μA
I _{IN}	Input current (F_SET)	V _O = V _{CC}				55	μA
V	Output voltage (F SET)	$I_O = 0 \text{ mA}$			1.4		V
Vo	Output voltage (F_SET)	$32 kΩ \le R_{PD} \le 78 kΩ$			785		mV
V _{OH}	Receiver high-level output voltage	I _{OH} = -4 mA		V _{CC} - 0.4	V _{CC} - 0.2		V
V _{OL}	Receiver low-level output voltage	I _{OL} = 4 mA			0.2	0.4	V
l _{OZ}	Receiver high-impedance output current	V _O = 0 V or V _{CC} , MODE = 0		-1		1	μΑ
Device							
	Supply current (quiescent)	OOK transmit mode	D = V _{CC} , MODE = V _{CC} , resistor between F_SET and GND, no load		3.1	5	Δ
I _{CC}		OOK receive mode	D = V _{CC} , MODE = GND, resistor between F_SET and GND, no load		4	6	mA
T _{SD}	Thermal shutdown temperature			160	170	185	°C
T _{HYS}	Thermal shutdown hysteresis				11	15	°C

⁽¹⁾ See OOK modulation section for the complete carrier frequency range



5.7 Power Dissipation Characteristics

Over operating free-air temperature range (unless otherwise noted). All typical values are at 25° C and supply voltage of $V_{CC} = 5 \text{ V}$.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
PDoo	Chip power dissipation in OOK mode	MODE = V _{CC} , R _L =	f ₀ = 125 kHz, 12.5 kHz (25 kbps) clock pattern as data		60	80	mW
К	Crip power dissipation in OOK mode	60 Ω, no C _L	f ₀ = 5 MHz, 500 kHz (1 Mbps) clock pattern as data		90	125	mW

5.8 Switching Characteristics

over operating free-air temperature range (unless otherwise noted). All typical values are at 25° C and supply voltage of $V_{CC} = 5 \text{ V}$.

PARAMETER		TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT
Driver						'	
t _r , t _f	Driver differential output rise and fall times				10	30	ns
t _{PHL} , t _{PLH}	Driver propagation delay	$R_L = 60 \Omega, C_L = 50 pF, S$	$R_L = 60 \Omega$, $C_L = 50 pF$, See Figure 6-4		1.2	2.5	Clocks
t _{SK(P)}	Driver pulse skew, t _{PHL} - t _{PLH}				0.3	2.5	Clocks
Receiver			·				
t _r , t _f	Receiver output rise and fall times	C _L = 15 pF, See Figure 6-5			1.5	16	ns
t _{PHL} , t _{PLH}	Receiver propagation delay time				4	6.5	Clocks
t _{SK(P)}	Receiver pulse skew, t _{PHL} - t _{PLH}				1.1		CIOCKS
Device			·				
t _{TX-RX_OOK}	Transmit to receive mode change delay, OOK mode	For all R _{FSET}	Worst case of t _{TX} . RX_OOK_ZERO and t _{TX} . RX_OOK_ONE. See Figure 6-6and Figure 6-7			14	clocks
t _{RX-TX_OOK}	Receive to transmit mode change delay, OOK mode	For all R _{FSET}	See Figure 6-8			12	clocks
t _{TX_TIMEOUT}	Transmit timeout delay			60	110		s



5.9 Typical Characteristics

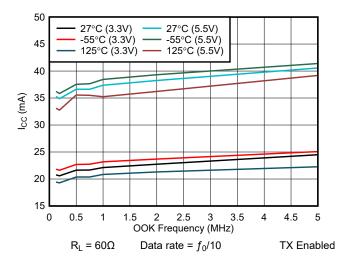


Figure 5-1. ICC vs OOK Frequency



6 Parameter Measurement Information

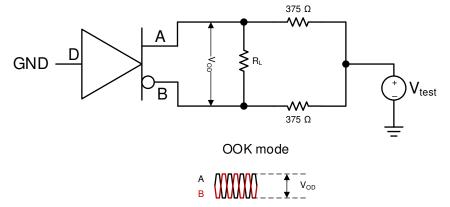


Figure 6-1. Measurement of Driver Differential Output Voltage With Common-Mode Load

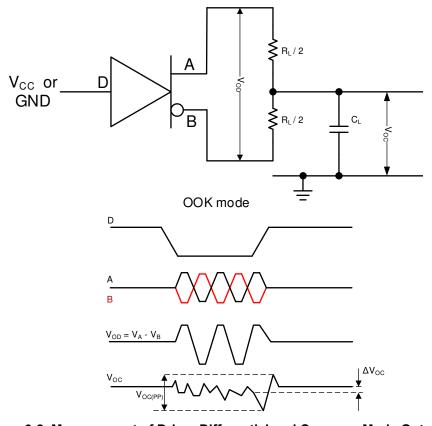


Figure 6-2. Measurement of Driver Differential and Common-Mode Outputs

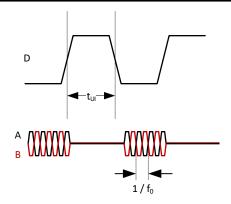


Figure 6-3. Measurement of Carrier Frequency

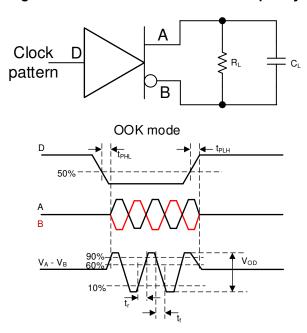


Figure 6-4. Measurement of Driver Switching Characteristics

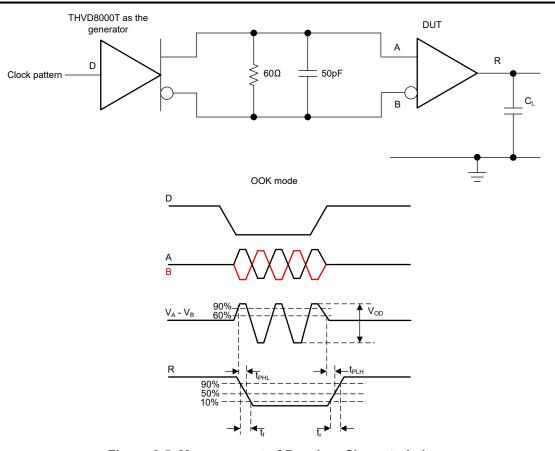
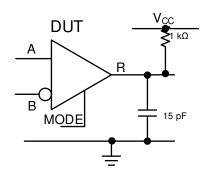


Figure 6-5. Measurement of Receiver Characteristics



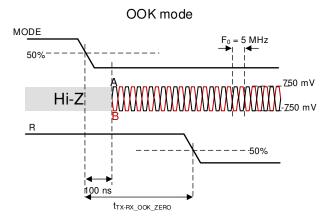
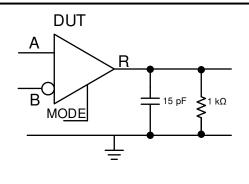


Figure 6-6. Transmit to Receive Mode Change with Low Output



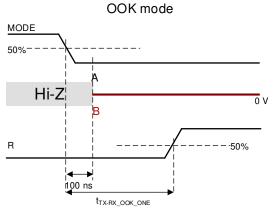


Figure 6-7. Transmit to Receive Mode Change with High Output

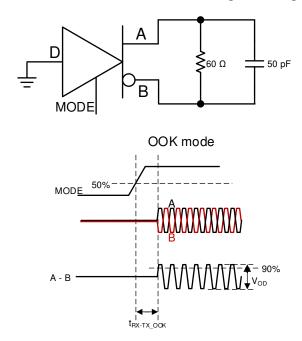


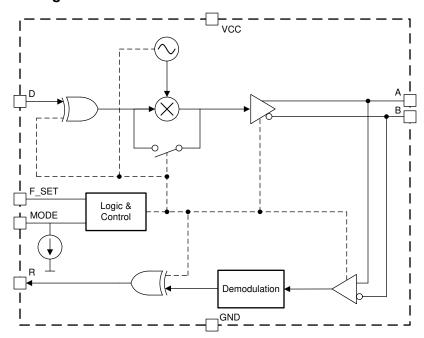
Figure 6-8. Receive to Transmit Mode Change

7 Detailed Description

7.1 Overview

THVD8000T enables power line communication using RS-485 physical layer signaling. An integrated OOK modulator enables RS-485 data to be directly coupled onto existing power cables via series capacitors without any updates to the MCU or the controller. The THVD8000T receiver extracts the data from the power cables through series capacitors by using a precise bandpass filter and a demodulator.

7.2 Functional Block Diagrams



7.3 Feature Description

7.3.1 OOK Modulation with F SET pin

Data at the D input is modulated with the carrier frequency (f_0) via the F_SET pin. Figure 7-1 illustrates the modulation scheme. A high level at the D input is driven to the mid-level with zero differential voltage (V_{OD}). A low level at the D input is modulated at the carrier frequency. The recommendation is to use a carrier frequency that is 10x higher than the data rate. Higher data rates are possible at the expense of increased pulse width distortion with the use of lower ratios.

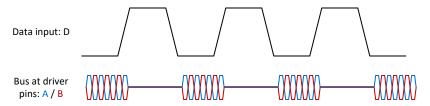


Figure 7-1. OOK Modulation Scheme

 f_0 is programmable by changing the external resistor (R_{F_SET}) value connected to ground. Table 7-1 shows the carrier frequency for the each recommended resistor value.

The oscillator used to generate the carrier frequency features spread spectrum clocking to reduce emissions.



Table 7-	·1. OOK f	o versus	R _{F SET}
----------	-----------	----------	--------------------

	1_021
R _{F_SET} (kΩ)	OOK f ₀ (kHz)
77	125
50	187.5
19	500
12.5	750
9.3	1000
4.4	2000
1.5	5000

7.3.2 OOK Demodulation

The OOK signal received at the A and B inputs go through a bandpass filter and a peak detector to regenerate the original data stream. Figure 7-2 shows the OOK input and the R output waveforms. The bandpass filter characteristics adapts to optimal settings automatically based on the carrier frequency, set via R_{F} SET.

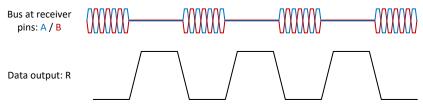


Figure 7-2. OOK Demodulation

7.3.3 Transmitter Timeout

The driver path incorporates a timeout feature to prevent a faulty node from occupying the bus indefinitely in a multi-drop application.

The driver stops transmitting and the outputs go high impedance if the D input does not detect an edge (either rising or falling) for longer than $t_{TX_TIMEOUT}$. One of the following events brings the device back to normal operation.

- Any edge at D input
- Toggle MODE pin

The transmit path resumes operation within t_{MODE}.

7.3.4 Polarity Free Operation

THVD8000T is immune to A and B polarity at the receiver input in OOK mode. The receiver data comparator only checks for the receive input signal magnitude, ignoring the polarity, to determine the logic level. Note that reversing the polarity does result in degraded pulse width distortion.

7.3.5 Glitch Free Mode Change

The device incorporates a delay of up to t_{MODE} when changing the state of the MODE pin. This feature makes sure there are no glitches at the A, B and R outputs when transitioning between transmit and receive modes.

7.3.6 Integrated IEC ESD and EFT Protection

Internal ESD protection circuits protect the transceiver against electrostatic discharges (ESD) according to IEC 61000-4-2 of up to ±8kV contact and against electrical fast transients (EFT) according to IEC 61000-4-4 of up to ±4kV. This integrated protection eliminates the need of external components reducing the system BOM.

7.4 Device Functional Modes

Table 7-2. THVD8000T Functional Modes

F_SET Configuration	Device Functional Mode
R _{F_SET} between F_SET and GND	OOK mode, f_0 set by the R_{F_SET} value
F_SET at high impedance	
F_SET at V _{CC}	Invalid, not recommended for normal operation
F_SET short to GND	

7.4.1 OOK Mode

Data at the D input is modulated with the carrier frequency set by the R_{F_SET} value when the device is transmitting (MODE = V_{CC}). See Section 7.3.1 section for more details. In receiving (MODE = GND), the device expects an OOK modulated signal at the A and B inputs. The data is demodulated and sent out via R pin. See Section 7.3.2 section for more details.

Table 7-3. Driver function table for OOK mode

INP	UTS		ОПТ	PUTS	FUNCTION
F_SET	MODE	D	Α	В	FUNCTION
	Н	H or Z	Bias to V _{CM}	Bias to V _{CM}	Driver is actively biased to V _{CM} on the bus
R _{F_SET} (See Table 7-1)	Н	L	Oscillating	Oscillating	Bus actively driven at carrier frequency
	L or Z	X	Z	Z	Driver disabled, device in receive mode

Table 7-4. Receiver function table for OOK mode

	INPUTS		OUTPUT	FUNCTION		
F_SET	MODE Input		R	IONOTION		
	L or Z	Oscillating at F_SET and V _{ID} > V _{MAG_ZERO}	L	Receive valid bus low		
	L or Z	Oscillating at F_SET and V _{MAG_ONE} ?		Receive invalid bus, output indeterminate		
R _{F_SET} (See Table 7-1)	L or Z	Oscillating at F_SET and V _{ID} < V _{MAG_ONE}	Н	Receive valid bus high		
	L or Z	Z / not oscillating	Н	Receive valid bus high		
	L or Z OPEN, SHORT, IDLE (V _{ID} = 0 V)		Н	Failsafe high output		
	Н	Х	Z	Receiver disabled, device in transmit mode		

7.4.2 Thermal shutdown (TSD)

The THVD8000T has a protection feature called thermal shutdown. When the junction temperature reaches T_{SD} , the device enters thermal shutdown protection mode. This mode disables the driver and receiver outputs, which will halt all communication through the device. Normal operation resume once the junction temperature drops out of thermal shutdown, which is typically T_{SD} - T_{HYS} .

8 Application Information Disclaimer

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application information

The THVD8000T is able to transmit data over an AC coupled power line pair using On-Off Keying (OOK).

8.2 Typical application (OOK mode)

To combine data and power over a single pair of wires, capacitors and inductors are used in a bias-tee configuration. High-frequency differential data is AC-coupled onto the bus lines via series capacitances while power is DC-coupled via series inductance. The values of these components depends on the carrier frequency, number of nodes on the bus, and the power delivery requirements (that is, voltage and total current sourced or consumed by a given node).

The transmitted differential communication signal is AC-coupled onto the power bus as shown below. This configuration provides the advantage that the power transmitted on the bus has little impact on the differential data, allowing for a wide range of voltage and current scenarios. Typical applications are realized with the THVD8000T transmitting over a power bus of 24VDC or 24VAC with currents from 100mA to 1A, but due to the AC-coupling the THVD8000T does not directly see these voltages. For more information, please refer to the THVD8000 design guide.

In Figure 8-1, there is an optional rectifier network pictured on the bus lines. This network of diodes makes sure the node is receives power correctly from the bus wires, even if the lines get swapped.

A termination resistance, R_T , is not required for device functionality but can be useful in improving signal integrity in some applications by reducing reflections that can occur at cable ends.

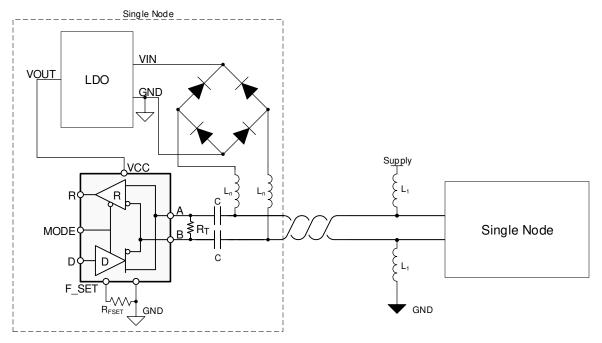


Figure 8-1. Typical Power Line Network with 2 Nodes



8.2.1 Design requirements

The main requirements are the values of the bus capacitors and the power inductors. Both of these values are dependant upon the carrier frequency selected.

8.2.1.1 Carrier frequency

This device uses on-off-keying to transmit binary data on the bus. Please read Section 7.3.1 for detailed information. The modulation and demodulation of the data can result in pulse width distortion due to asymmetries in low-to-high and high-to-low transition times. These asymmetries are due to factors like synchronization of the data to the internal carrier oscillator in the transmit path and the response time of the band-pass filter in the receive path. The impact of these factors can be minimized by choosing a carrier frequency much higher than the data rate required. A frequency ratio of at least 10:1 is recommended.

8.2.2 Detailed design procedure

8.2.2.1 Inductor value selection

Please note the inductor selected must also take power consumption into consideration. The inductor must be sized to handle the maximum anticipated current in addition to the inductance value.

The parallel aggregate impedance should be selected so the total equivalent impedance at the carrier frequency is $Z \ge 375\Omega$. This assumes RS-485 loading with 60Ω termination. If no termination is used in the application, then the total equivalent impedance at the carrier frequency could be reduced to $Z \ge 60\Omega$. These examples assume that termination is used. Equation 1 shows the parallel aggregate impedance equation for inductors L_1 to L_n . Since the inductance value for each node should be the same, the user determines that each nodes impedance is n times the total equivalent impedance. For example, if there are 4 nodes connected to the bus and the equivalent impedance is 375Ω , then each node impedance should be $1,500\Omega$.

$$Z = Z_1 ||Z_2|| ... ||Z_n$$
 (1)

To determine the suggested inductance value, Equation 2 can be rearranged to determine L_n , as shown in Equation 3.

$$Z_n = 2\pi f_0 L_n \tag{2}$$

$$L_n = \frac{Z_n}{2\pi f_0} \tag{3}$$

 f_0 is the carrier frequency (OOK frequency) used. If the previous $1.5 \mathrm{k}\Omega$ impedance per node is assumed with a carrier frequency of 1MHz, the resulting inductance limit is approximately 240 μ H per node. Note that this is the minimum suggested value per node. Refer to Figure 8-2 as a quick reference on the minimum inductance value to achieve 375Ω of total aggregate impedance. The value can be multiplied by the number of nodes on the bus to get the minimum inductance per node. Referring to the previous example, with 4 nodes and a carrier frequency of 1MHz, the minimum aggregate inductance is about 60μ H, which is 24μ H when multiplied by 4.

8.2.2.2 Capacitor value selection

Capacitor selection is easier than inductor selection, primarily because capacitance impedance is important to allow higher frequency signals through. However, the capacitor ratings for voltage must be carefully selected to meet the application requirements. Special considerations for hot plug nodes should be made to make sure the voltage transients during hot plugging do not exceed the absolute maximum values. See the *Absolute Maximum Ratings*.

The number of nodes on the bus does not play into the capacitance calculation. The impedance of a capacitor is shown in Equation 4.

$$Z = \frac{1}{2\pi f_0 C} \tag{4}$$

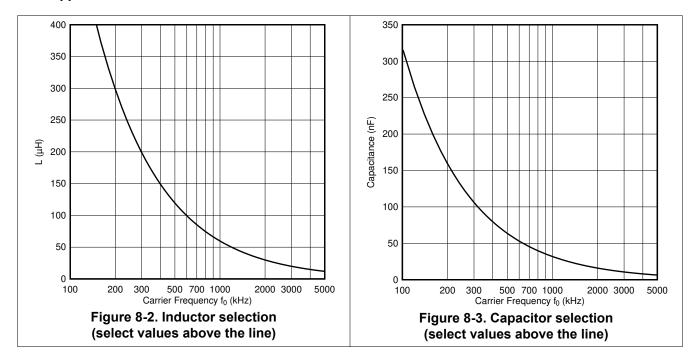


Maintaining $Z \le 5\Omega$ keeps the impedance low enough at the carrier frequency to allow data to pass through. If the equation is rearranged to calculate C, the result is shown in Equation 5.

$$C = \frac{1}{2\pi f_0 Z} \tag{5}$$

If the previous example of a 1MHz carrier frequency is used, then a minimum capacitance value of about 32nF. For a quick reference, refer to Figure 8-3.

8.2.3 Application Curves



8.3 Power supply recommendations

For reliable operation at all data rates and supply voltages, the supply should be decoupled with a 100nF to 220nF ceramic capacitor and a 1 μ F capacitor (for ESD sensitive designs) located as close to the supply pins as possible. This helps to reduce supply voltage ripple present on the outputs of switched-mode power supplies and also helps to compensate for the resistance and inductance of the PCB power planes.



8.4 Layout

8.4.1 Layout guidelines

Robust and reliable bus node design often requires the use of external transient protection devices to protect against surge transients that may occur in industrial environments. Since these transients have a wide frequency bandwidth (from approximately 3MHz to 300MHz), high-frequency layout techniques should be applied during PCB design.

- 1. Place the protection circuitry close to the bus connector to prevent noise transients from propagating across the board.
- 2. Use V_{CC} and ground planes to provide low inductance. Note that high-frequency currents tend to follow the path of least impedance and not the path of least resistance.
- 3. Place F SET components near the pin to keep capacitance load below recommended value
- 4. Use a pull up or down resistor on mode to set a default state
- 5. Apply 100nF to 220nF decoupling capacitors as close as possible to the V_{CC} pins of transceiver, UART and/or controller ICs on the board.
- 6. Use at least two vias for V_{CC} and ground connections of decoupling capacitors and protection devices to minimize effective via inductance.
- 7. Use $1k\Omega$ to $10k\Omega$ pull-up and pull-down resistors for enable lines to limit noise currents in these lines during transient events.
- 8. Insert pulse-proof resistors into the A and B bus lines if the TVS clamping voltage is higher than the specified maximum voltage of the transceiver bus pins. These resistors limit the residual clamping current into the transceiver and prevent it from latching up.
- 9. While pure TVS protection is sufficient for surge transients up to 1kV, higher transients require metal-oxide varistors (MOVs) which reduce the transients to a few hundred volts of clamping voltage, and transient blocking units (TBUs) that limit transient current to less than 1mA.

8.4.2 Layout Example

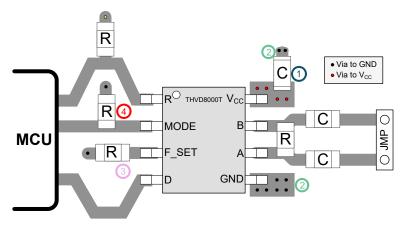


Figure 8-4. Layout Example (OOK)

9 Device and Documentation Support

9.1 Device Support

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
March 2025	*	Initial Release

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
THVD8000TDDFR	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-55 to 125	8000T
THVD8000TDDFR.A	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-55 to 125	8000T

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

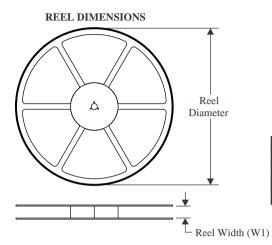
⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

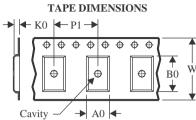
⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

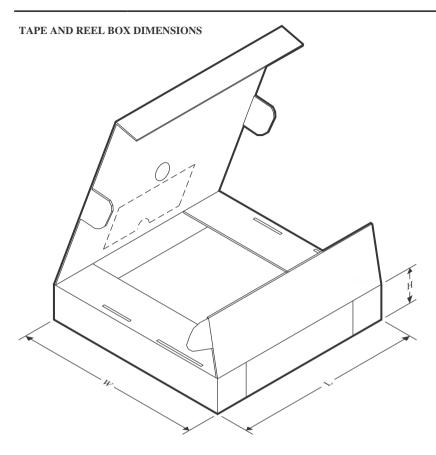


*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THVD8000TDDFR	SOT-23- THIN	DDF	8	3000	180.0	9.5	3.17	3.1	1.1	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

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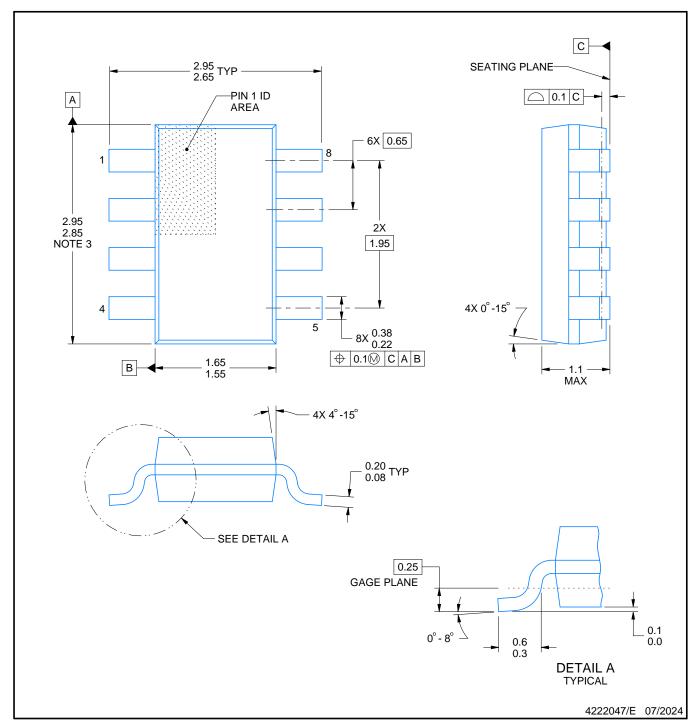


*All dimensions are nominal

Ì	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
ı	THVD8000TDDFR	SOT-23-THIN	DDF	8	3000	205.0	200.0	30.0	



PLASTIC SMALL OUTLINE



NOTES:

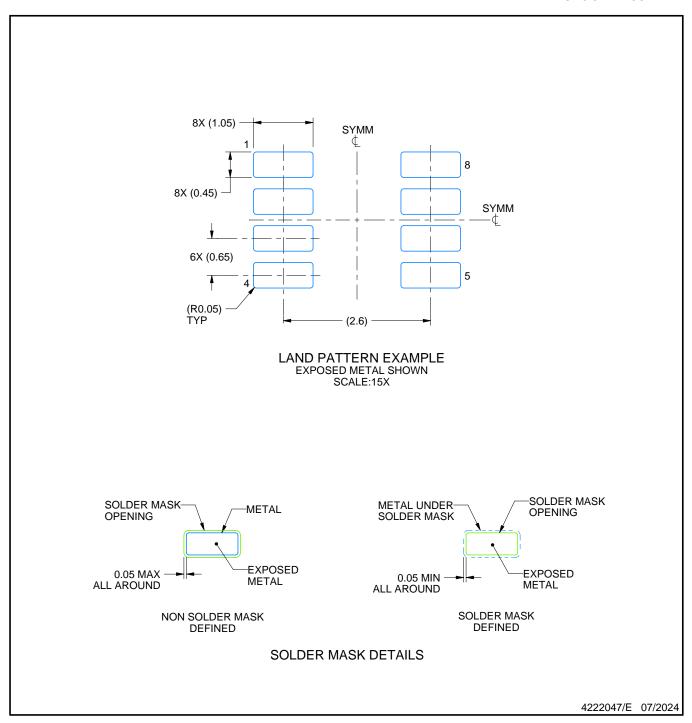
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.



PLASTIC SMALL OUTLINE

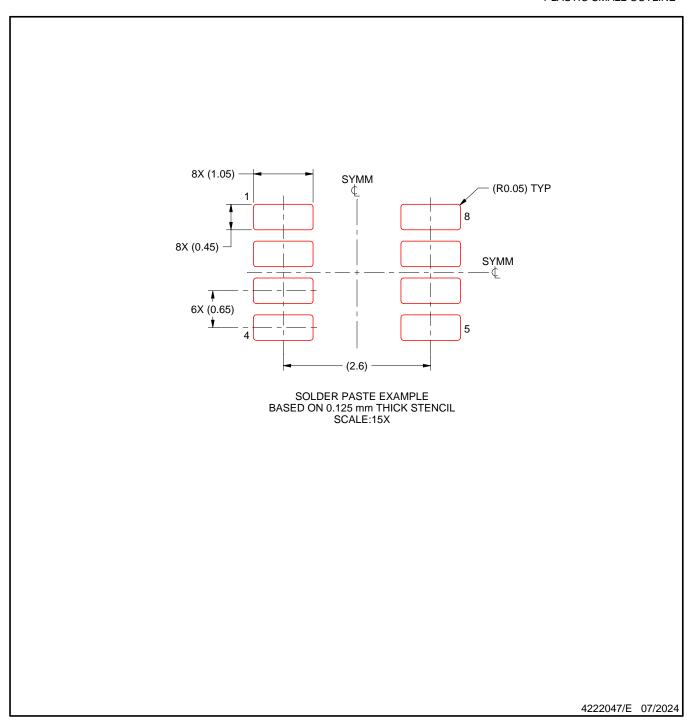


NOTES: (continued)

- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 7. Board assembly site may have different recommendations for stencil design.



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